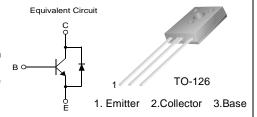


KSC5302DM

High Voltage & High Speed Power Switch Application

- High breakdown Voltage :BV_{CBO}=800V
- Built-in Free-wheeling Diode makes efficient anti saturation operation
- Suitable for half bridge light ballast Applications
- No need to interest an h_{FE} value because of low variable storage-time spread even though corner spirit product
- Low base drive requirement



NPN Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	800	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	12	V
I _C	Collector Current (DC)	2	А
I _{CP}	*Collector Current (Pulse)	5	А
I _B	Base Current (DC)	1	А
I _{BP}	*Base Current (Pulse)	2	А
P _C	Power Dissipation(T _C =25°C)	25	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Thermal Characteristics $\rm T_{C} = 25^{\circ}C$ unless otherwise noted

Symbol	Characteristics		Rating	Unit
$R_{\theta jc}$	Thermal Resistance	Junction to Case	5.0	°C/W
$R_{\theta ja}$		Junction to Ambient	62.5	

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Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =1mA, I _E =0	800	-	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C=5$ mA, $I_B=0$	400	-	-	V
BV _{EBO}	Emitter Cut-off Current	I _E =1mA, I _C =0	12	-	-	V
I _{CBO}	Collector Cut-off Current	V _{CB} =500V, I _E =0	-	-	10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 9V, I_{C} = 0$	-	-	10	μΑ
h _{FE1}	DC Current Gain	V _{CE} =1V, I _C =0.4A	20	-	-	
h _{FE2}		$V_{CE}=1V,I_{C}=1A$	10	-	-	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =0.4A, I _B =0.04A	-	-	0.4	V
		I _C =1A, I _B =0.2A	-	-	0.5	V
V _{BE} (sat)	Collector-Emitter Saturation Voltage	I _C =0.4A, I _B =0.04A	-	-	0.9	V
		I _C =1A, I _B =0.2A	-	-	1.0	V
C _{ob}	Output Capacitance	VCB = 10V, f=1MHz	-	-	75	pF
t _{ON}	Turn On Time	V_{CC} =300V, I_{C} =1A	-	-	150	ns
t _{STG}	Storage Time	$I_{B1} = 0.2A, I_{B2} = -0.5A$	-	-	2	μs
t _F	Fall Time	$R_L = 300\Omega$	-	-	0.2	μs
t _{STG}	Storage Time	V _{CC} =15V, V _Z =300V	-	-	2.35	μs
t _F	Fall Time	$I_C = 0.8A, I_{B1} = 0.16A$ $I_{B2} = -0.16A, L_C = 200\mu H$	-	-	150	ns
V _F	Diode Forward Voltage	I _F = 0.4A	-	-	1.2	V
•		I _F = 1A	-	-	1.5	V
t _{rr}	* Reverse Recovery Time	I _F = 0.2A	-	800	-	ns
	$(di/dt = 10A/\mu s)$	I _F = 0.4A	-	1	-	μs
		I _F = 1A	-	1.4	-	μs

*Pulse Test : Pulse Width=5mS, Duty cycles ≤ 10%

Typical Characteristics

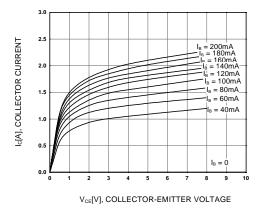


Figure 1. Static Characteristic

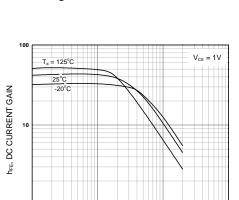


Figure 3. DC current Gain

Ic[A], COLLECTOR CURRENT

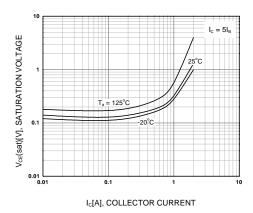


Figure 5. Collector-Emitter Saturation Voltage

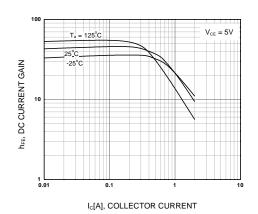


Figure 2. DC current Gain

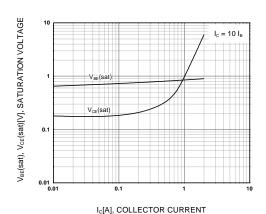


Figure 4. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

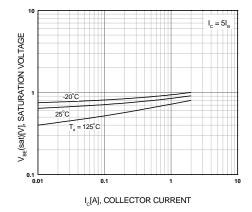


Figure 6. Base-Emitter Saturation Voltage

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Typical Characteristics (Continued)

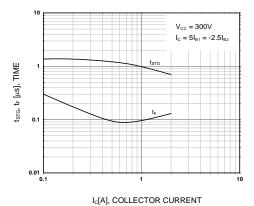


Figure 7. Switching Time

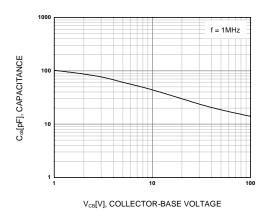


Figure 8. Collector Output Capacitance

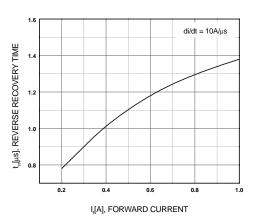


Figure 9. Reverse Recovery Time

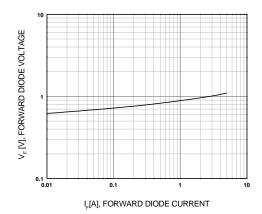
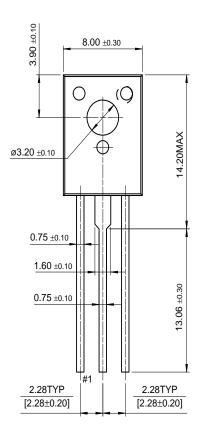
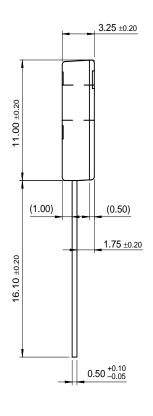


Figure 10. Forward Diode Voltage

Package Demensions

TO-126







Dimensions in Millimeters

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